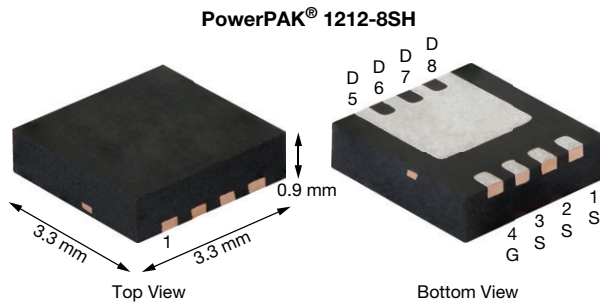


## P-Channel 30 V (D-S) MOSFET



PRODUCT SUMMARY	
$V_{DS}$ (V)	-30
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = -10$ V	0.0072
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = -4.5$ V	0.0130
$Q_g$ typ. (nC)	32
$I_D$ (A)	-35 <sup>d</sup>
Configuration	Single

### FEATURES

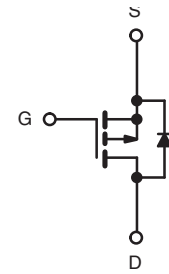
- TrenchFET<sup>®</sup> power MOSFET
- 100 %  $R_g$  and UIS tested
- Material categorization:  
For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Notebook adapter switch
- Notebook battery management
- Load switch



P-Channel MOSFET

### ORDERING INFORMATION

Package	PowerPAK 1212-8
Lead (Pb)-free and halogen-free	SiSH101DN-T1-GE3

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	$V_{DS}$	-30	V	
Gate-source voltage	$V_{GS}$	$\pm 25$		
Continuous drain current ( $T_J = 150$ °C)	$I_D$	$T_C = 25$ °C	-35 <sup>d</sup>	
		$T_C = 70$ °C	-35 <sup>d</sup>	
		$T_A = 25$ °C	-16.9 <sup>a, b</sup>	
		$T_A = 70$ °C	-13.6 <sup>a, b</sup>	
Pulsed drain current ( $t = 300$ $\mu$ s)	$I_{DM}$	-80	A	
Continuous source-drain diode current	$I_S$	$T_C = 25$ °C		-35 <sup>d</sup>
		$T_A = 25$ °C		-3 <sup>a, b</sup>
Avalanche current	$I_{AS}$	-20	mJ	
Single-pulse avalanche energy	$E_{AS}$	20		
Maximum power dissipation	$P_D$	$T_C = 25$ °C	52	
		$T_C = 70$ °C	33	
		$T_A = 25$ °C	3.7 <sup>a, b</sup>	
		$T_A = 70$ °C	2.4 <sup>a, b</sup>	
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +150	°C	
Soldering recommendations (peak temperature) <sup>e, f</sup>		260		

### THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient <sup>a, c</sup>	$R_{thJA}$	26	33	°C/W
Maximum junction-to-case	$R_{thJC}$	1.9	2.4	

#### Notes

- Surface mounted on 1" x 1" FR4 board
- $t = 10$  s
- Maximum under steady state conditions is 81 °C/W
- Package limited
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA	-30	-	-	V
V <sub>DS</sub> temperature coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = -250 μA	-	-22	-	mV/°C
V <sub>GS(th)</sub> temperature coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>		-	5.1	-	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-1.2	-	-2.5	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 25 V	-	-	± 100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V	-	-	-1	μA
		V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C	-	-	-5	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ -10 V, V <sub>GS</sub> = -10 V	-30	-	-	A
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -15 A	-	0.0058	0.0072	Ω
		V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -10 A	-	0.0100	0.0130	
Forward transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = -0 V, I <sub>D</sub> = -15 A	-	44	-	S
<b>Dynamic <sup>b</sup></b>						
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -15 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	3595	-	pF
Output capacitance	C <sub>oss</sub>		-	442	-	
Reverse transfer capacitance	C <sub>rss</sub>		-	408	-	
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> = -15 V, V <sub>GS</sub> = -10 V, I <sub>D</sub> = -10 A	-	68	102	nC
		V <sub>DS</sub> = -15 V, V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -10 A	-	32	48	
Gate-source charge	Q <sub>gs</sub>		-	9	-	
Gate-drain charge	Q <sub>gd</sub>	-	12.2	-		
Gate resistance	R <sub>g</sub>	f = 1 MHz	0.4	1.8	3.6	Ω
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = -15 V, R <sub>L</sub> = 1.5 Ω I <sub>D</sub> ≅ -10 A, V <sub>GEN</sub> = -10 V, R <sub>g</sub> = 1 Ω	-	12	24	ns
Rise time	t <sub>r</sub>		-	10	20	
Turn-off delay time	t <sub>d(off)</sub>		-	38	75	
Fall time	t <sub>f</sub>		-	8	16	
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = -15 V, R <sub>L</sub> = 1.5 Ω I <sub>D</sub> ≅ -10 A, V <sub>GEN</sub> = -4.5 V, R <sub>g</sub> = 1 Ω	-	52	100	
Rise time	t <sub>r</sub>		-	82	150	
Turn-off delay time	t <sub>d(off)</sub>		-	38	75	
Fall time	t <sub>f</sub>		-	15	30	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous source-drain diode current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	-35	A
Pulse diode forward current	I <sub>SM</sub>		-	-	-80	
Body diode voltage	V <sub>SD</sub>	I <sub>S</sub> = -3 A, V <sub>GS</sub> = 0 V	-	-0.76	-1.2	V
Body diode reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = -10 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C	-	21	40	ns
Body diode reverse recovery charge	Q <sub>rr</sub>		-	10	20	nC
Reverse recovery fall time	t <sub>a</sub>		-	9	-	ns
Reverse recovery rise time	t <sub>b</sub>		-	12	-	

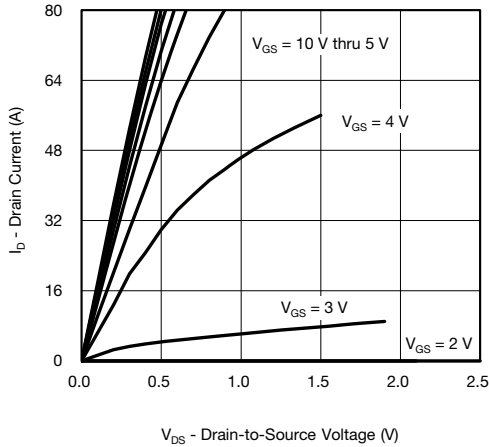
**Notes**

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %  
b. Guaranteed by design, not subject to production testing

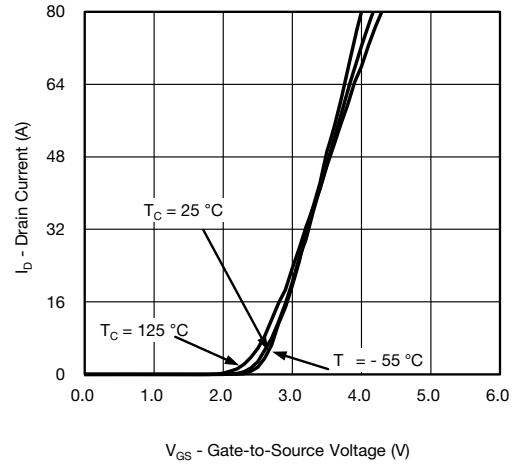
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



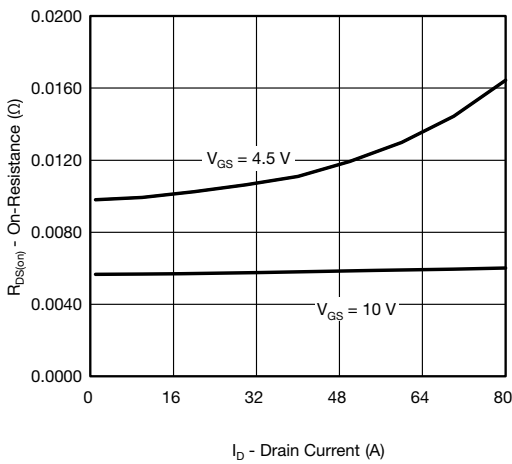
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



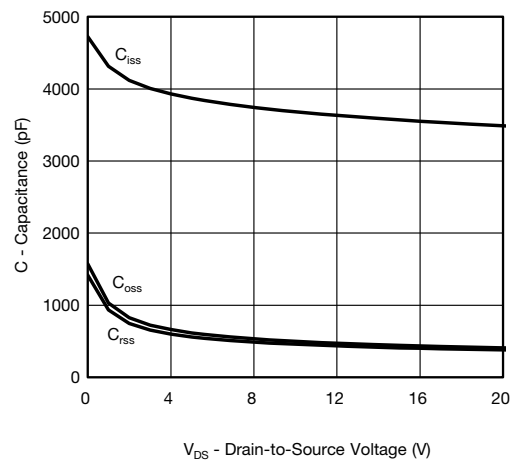
Output Characteristics



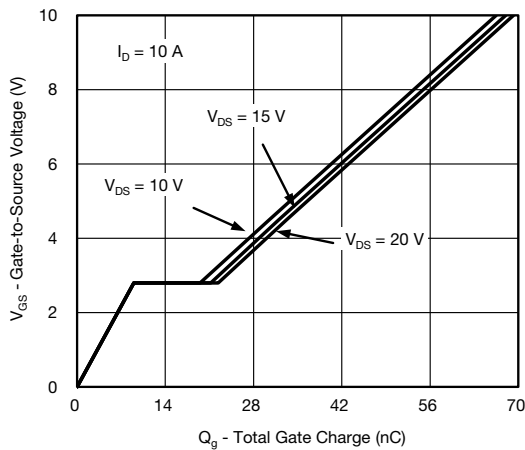
Transfer Characteristics



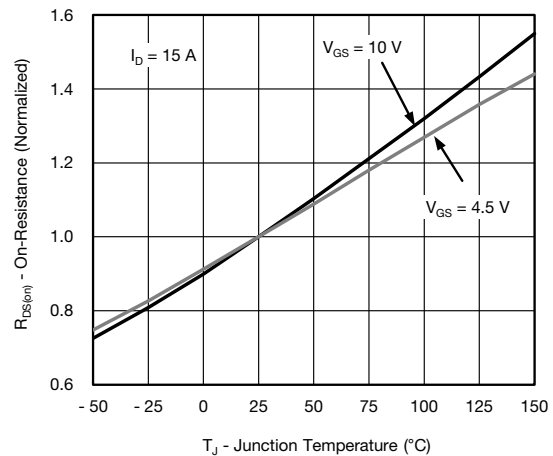
On-Resistance vs. Drain Current



Capacitance



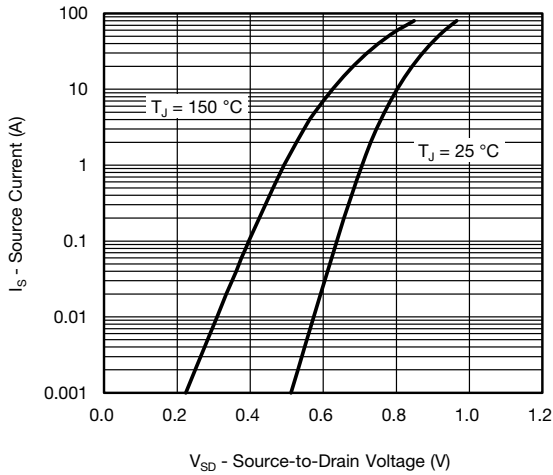
Gate Charge



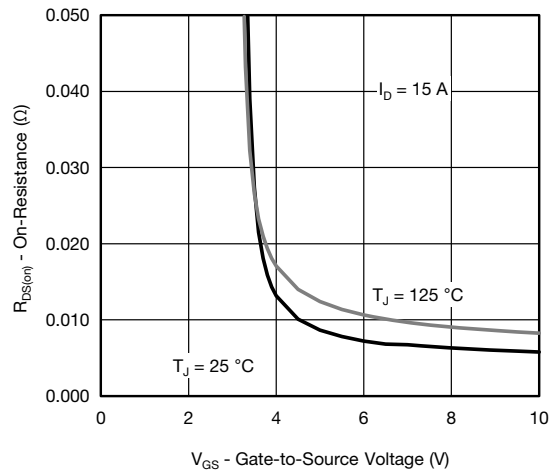
On-Resistance vs. Junction Temperature



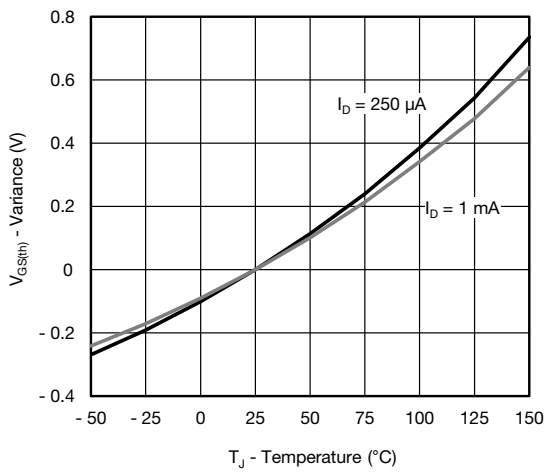
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



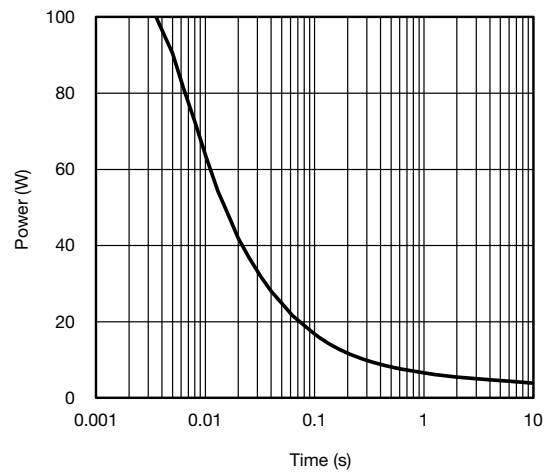
**Source-Drain Diode Forward Voltage**



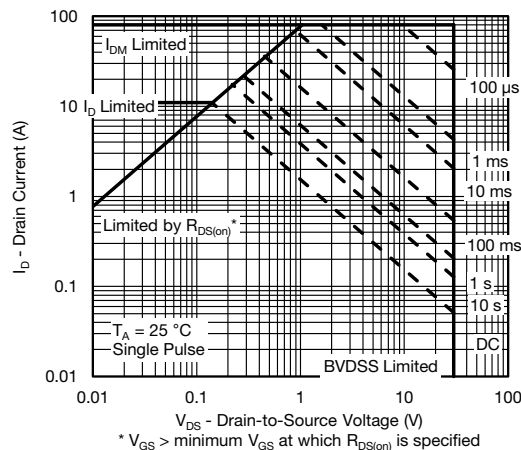
**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**



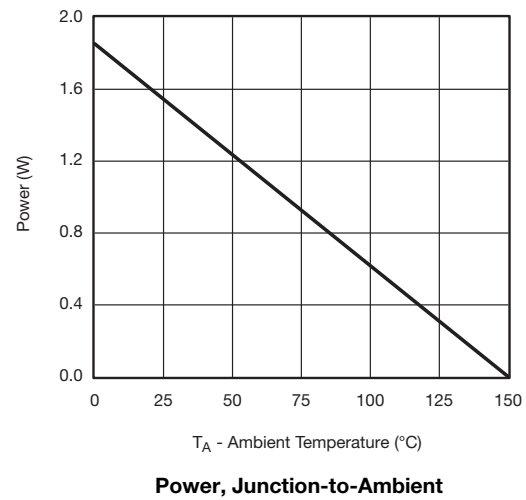
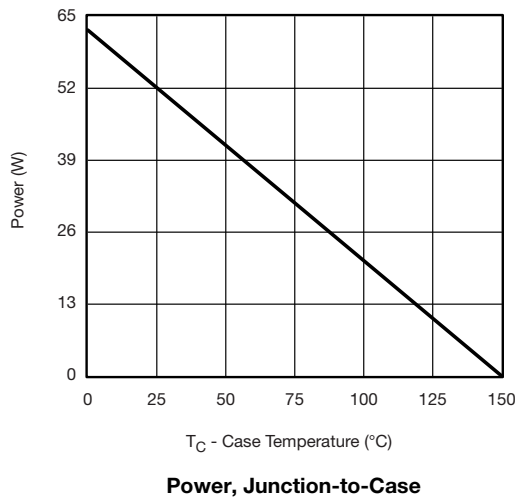
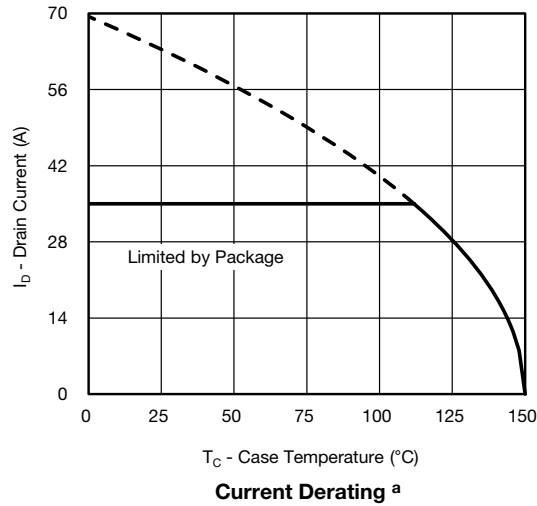
**Single Pulse Power, Junction-to-Ambient**



**Safe Operating Area**



MOSFET TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

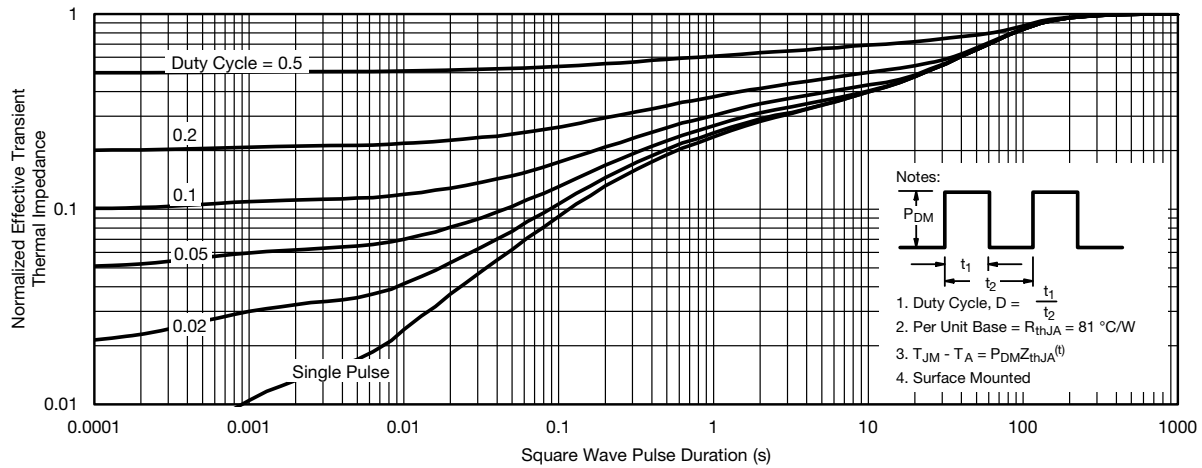


Note

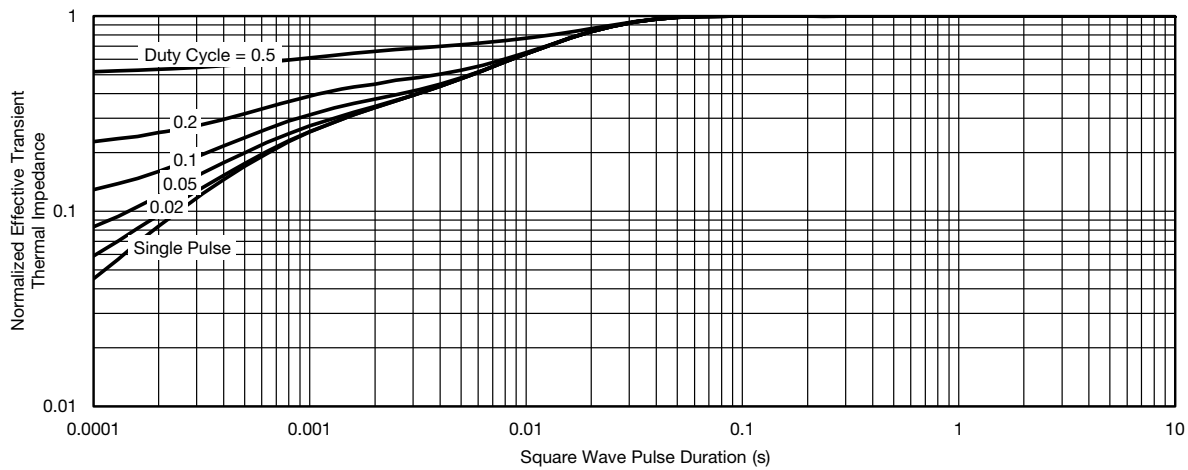
- a. The power dissipation P<sub>D</sub> is based on T<sub>J</sub> max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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## Case Outline for PowerPAK<sup>®</sup> 1212-SWLH and PowerPAK<sup>®</sup> 1212-8SH



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.82	0.90	0.98	0.032	0.035	0.038
A1	0.00	-	0.05	0.000	-	0.002
A3	0.20 ref.			0.008 ref.		
b	0.25	0.30	0.35	0.010	0.012	0.014
D	3.20	3.30	3.40	0.126	0.130	0.134
D1	2.15	2.25	2.35	0.085	0.089	0.093
E	3.20	3.30	3.40	0.126	0.130	0.134
E1	1.60	1.70	1.80	0.063	0.067	0.071
e	0.65 bsc.			0.026 bsc.		
K	0.76 ref.			0.030 ref.		
K1	0.41 ref.			0.016 ref.		
L	0.33	0.43	0.53	0.013	0.017	0.021
Z	0.525 ref.			0.021 ref.		
ECN: S20-0930-Rev. C, 07-Dec-2020						
DWG: 6062						

## RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads  
Dimensions in Inches/(mm)

[Return to Index](#)





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